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REVISION HISTORY

10/12—Rev. B to Rev. C

Updated Format	Universal
Added Pin Descriptions, Table 3	5
Moved Table 4	5
Changes to Figure 5, Figure 6, Figure 8, and Figure 9.	6
Updated Outline Dimensions	13
Changes to Ordering Guide	14

9/02—Rev. A to Rev. B

SPECIFICATIONS

 V_{DD} = +15 V, V_{SS} = -15 V, V_{L} = 5 V, unless otherwise noted.

Table 1.

	25°C -40°C to +85°C							
Parameter	Min	Тур	Max	Min	Тур	Max	Unit	Test Conditions/Comments
ANALOG SWITCH								
Analog Signal Range		±15			±15		V	
Ron			115			175	Ω	$-10 \text{ V} \le \text{V}_S \le +10 \text{ V}$, $I_{DS} = 1 \text{ mA}$, see Figure 21
R_{ON} vs. V_D (V_S)		20					%	
Ron Drift		0.5					%/°C	
R _{ON} Match		5					%	$V_S = 0 \text{ V, } I_{DS} = 1 \text{ mA}$
LEAKAGE CURRENTS								
I _s (Off)		0.5					nA	$V_D = \pm 14 \text{ V}$; $V_S = \mp 14 \text{ V}$; see Figure 22
Off Input Leakage			5			100	nA	
I _D (Off)		0.5					nA	$V_D = \pm 14 \text{ V}$; $V_S = \mp 14 \text{ V}$; see Figure 22
Off Output Leakage			5			100	nA	
I _D (On)		0.5					nA	$V_D = V_S = \pm 14 \text{ V}$; see Figure 23
On Channel Leakage			5			200	nA	_
DIGITAL CONTROL								
V _{INH} , Input High Voltage				2.4			V	TTL compatibility is independent of V _L
V _{INL} , Input Low Voltage						8.0	V	
I _{NL} or I _{NH}						1	μΑ	
C _{IN} , Digital Input Capacitance		5					рF	
DYNAMIC CHARACTERISTICS								
t _{OPEN} ¹		30					ns	See Figure 24
ton ¹			600				ns	See Figure 25
t _{OFF} ¹			450				ns	See Figure 25
Off Isolation		80					dB	V_S = 10 V (p-p); f = 100 kHz; R _L = 75 Ω; see Figure 26
Channel-to-Channel Crosstalk		80					dB	See Figure 27
C _s (Off)		5					рF	
C _D (Off)		5					рF	
C_S , C_D (On)		16					pF	
Q _{INJ} , Charge Injection		20					рC	$R_S = 0 \Omega$; $C_L = 1000 \text{ pF}$; $V_S = 0 \text{ V}$; see Figure 28
POWER SUPPLY								
IDD		0.6					mA	Digital inputs = V _{INL} or V _{INH}
I _{DD}			1				mA	
Iss		0.1					mA	
Iss			0.2				mA	
I _L			0.9				mA	

 $^{^{\}rm 1}\,\text{Sample}$ tested at 25°C to ensure compliance.

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25$ °C, unless otherwise stated.

Table 2.

Parameter	Rating
V _{DD} to V _{SS}	44 V
V _{DD} to GND	25 V
V _{SS} to GND	−25 V
V_L to GND	−0.3 V, 25 V
Analog Inputs ¹	
Voltage at S, D	$V_{SS} - 0.3 \text{ V to } V_{DD} + 0.3 \text{ V}$
Continuous Current, S or D	30 mA
Pulsed Current S or D	
1 ms Duration, 10% Duty Cycle	70 mA
Digital Inputs ¹	
Voltage at IN	$V_{SS} - 2 V \text{ to } V_{DD} + 2 V \text{ or}$
	20 mA, Whichever
	Occurs First
Power Dissipation (Any Package)	
Up to +75°C	470 mW
Derates above +75°C by	6 mW/°C
Operating Temperature	−40°C to +85°C
Storage Temperature Range	−65°C to +150°C
Lead Temperature (Soldering 10 sec)	+300°C

¹ Overvoltage at IN, S, or D will be clamped by diodes. Current should be limited to the Maximum Rating listed in Table 2.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

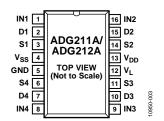


Figure 3. PDIP, SOIC Pin Configuration

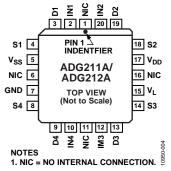


Figure 4. PLCC Pin Configuration

Table 3. Pin Function Descriptions

Pin No. PDIP, SOIC PLCC			Description		
		Mnemonic			
1	2	IN1	Logic Control Input.		
2	3	D1	Drain Terminal. Can be an input or output.		
3	4	S1	Source Terminal. Can be an input or output.		
4	5	V _{SS}	Most Negative Power Supply Potential.		
5	7	GND	Ground (0 V) Reference.		
6	8	S4	Source Terminal. Can be an input or output.		
7	9	D4	Drain Terminal. Can be an input or output.		
8	10	IN4	Logic Control Input.		
9	12	IN3	Logic Control Input.		
10	13	D3	Drain Terminal. Can be an input or output.		
11	14	S3	Source Terminal. Can be an input or output.		
12	15	VL	Logic Supply Voltage.		
13	17	V_{DD}	Most Positive Power Supply Potential.		
14	18	S2	Source Terminal. Can be an input or output.		
15	19	D2	Drain Terminal. Can be an input or output.		
16	20	IN2	Logic Control Input.		
	1, 6, 11, 16	NIC	No Internal Connection.		

Table 4. Truth Table

ADG211A In	ADG212A In	Switch Condition
0	1	On
1	0	Off

TYPICAL PERFORMANCE CHARACTERISTICS

The switches can comfortably operate anywhere in the 10 V to 15 V single or dual supply range, with only a slight degradation in performance. The following graphs show the relevant performance curves. The test circuits and test conditions are given in a following section, Test Circuits.

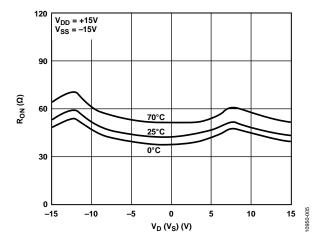


Figure 5. R_{ON} as a Function of V_D (V_S), Dual ± 15 V Supplies

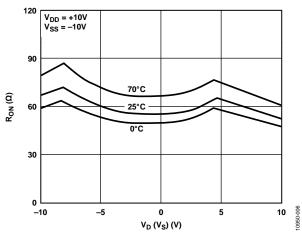


Figure 6. R_{ON} as a Function of V_D (V_S), Dual ± 10 V Supplies

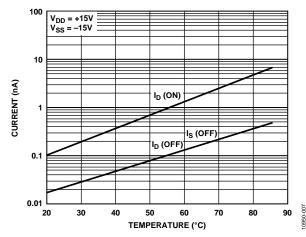


Figure 7. Leakage Current as a Function of Temperature (Note That Leakage Current Reduces as the Supply Voltages Reduce)

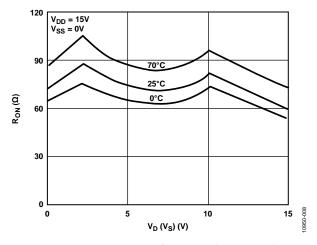


Figure 8. R_{ON} as a Function of V_D (V_S), Single +15 V Supply

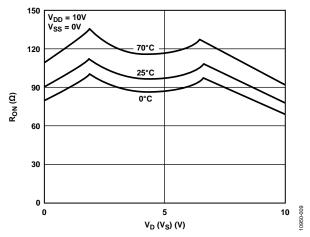


Figure 9. R_{ON} as a Function of V_D (V_S), Single +10 V Supply

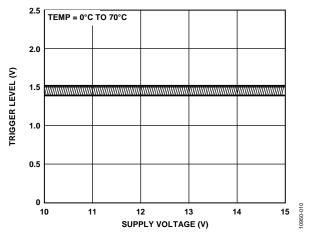


Figure 10. Trigger Levels vs. Power Supply Voltage, Dual or Single Supply Voltage

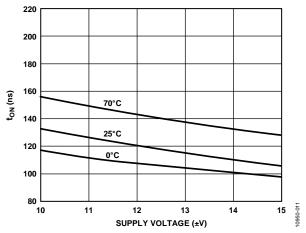


Figure 11. ton vs. Supply Voltage (Dual Supply)

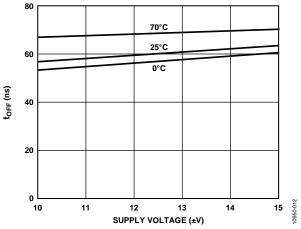


Figure 12. t_{OFF} vs. Supply Voltage (Dual Supply)

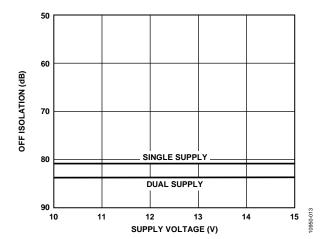


Figure 13. Off Isolation and Channel-to-Channel Crosstalk vs. Supply Voltage

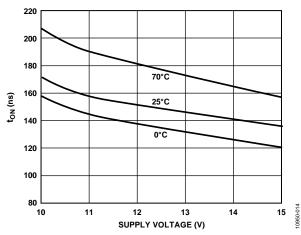


Figure 14. t_{ON} vs. Supply Voltage (Single Supply)

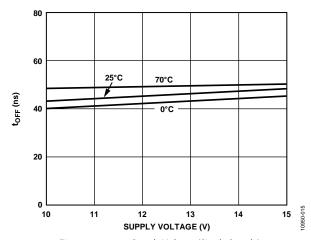


Figure 15. t_{OFF} vs. Supply Voltage (Single Supply)

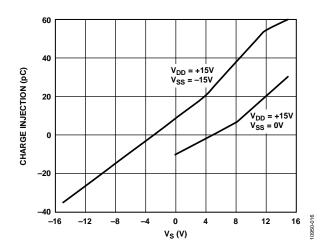


Figure 16. Charge Injection vs. Source Voltage (V_s) for Dual and Single 15 V Supplies

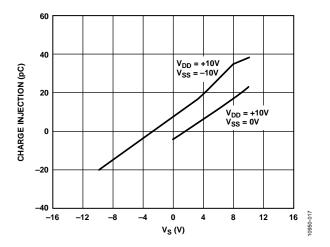


Figure 17. Charge Injection vs. Source Voltage for Dual and Single 10 V Supplies

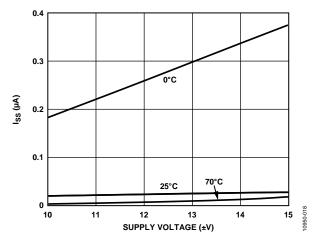


Figure 18. Iss vs. Supply Voltage (Dual Supply)

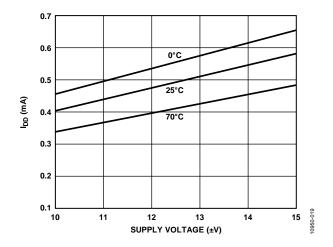


Figure 19. I_{DD} vs. Supply Voltage, (Dual Supply)

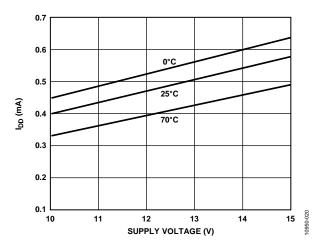


Figure 20. I_{DD} vs. Supply Voltage (Single Supply)

TERMINOLOGY

Ron

Ohmic resistance between the out and S terminals.

Ron Match

Difference between the R_{ON} of any two channels.

Is (Off)

Source terminal leakage current when the switch is off.

I_D (Off)

Drain terminal leakage current when the switch is off.

I_D (On)

Leakage current that flows from the closed switch into the body.

 $V_D(V_S)$

Analog voltage on the D, S terminals.

Cs (Off)

Switch input capacitance off condition.

C_D (Off)

Switch output capacitance off condition.

 C_{IN}

Digital input capacitance.

 C_D , C_S (On)

Input or output capacitance when the switch is on.

ton

Delay time between the 50% and 90% points of the digital input and switch on condition.

toff

Delay time between the 50% and 90% points of the digital input and switch off condition.

topen

Off time measured between 50% points of both switches, which are connected as a multiplexer when switching from one address state to another.

 V_{INL}

Maximum input voltage for a logic low.

 V_{INI}

Minimum input voltage for a logic high.

 $I_{INL}(I_{INH})$

Input current of the digital input.

 V_{DD}

Most positive voltage supply.

 \mathbf{V}_{ss}

Most negative voltage supply.

 \mathbf{V}_{L}

Logic supply voltage.

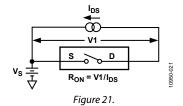
 I_{DD}

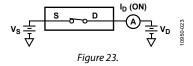
Positive supply current.

 \mathbf{I}_{SS}

Negative supply current.

TEST CIRCUITS





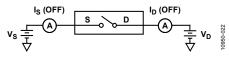


Figure 22.

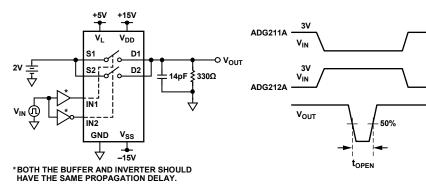
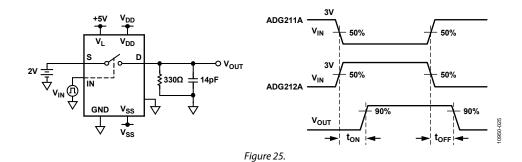


Figure 24.



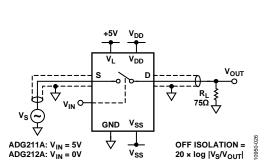


Figure 26. Off Isolation

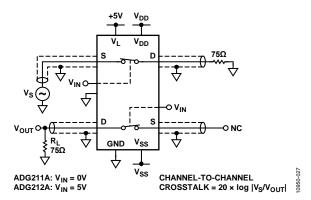
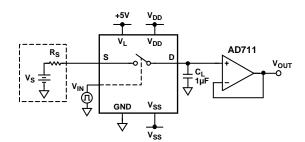


Figure 27. Channel-to-Channel Crosstalk



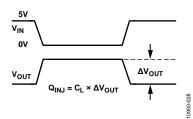
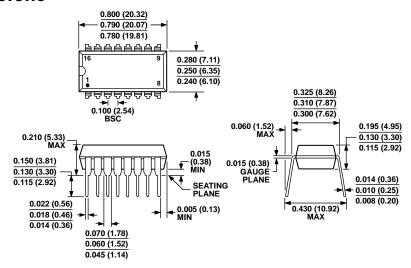


Figure 28. Charge Injection

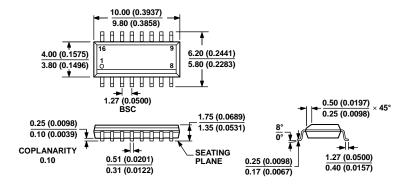
OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MS-001-AB

CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN. CORNER LEADS MAY BE CONFIGURED AS WHOLE OR HALF LEADS.

Figure 29. 16-Lead Plastic Dual In-Line Package [PDIP] Narrow Body (N-16) Dimensions shown in inches and (millimeters)

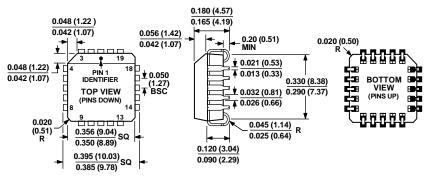


COMPLIANT TO JEDEC STANDARDS MS-012-AC

CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 30.16-Lead Standard Small Outline Package [SOIC_N] Narrow Body (R-16) Dimensions shown in millimeters and (inches)

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COMPLIANT TO JEDEC STANDARDS MO-047-AA
CONTROLLING DIMENSIONS ARE IN INCHES; MILLIMETER DIMENSIONS
(IN PARENTHESES) ARE ROUNDED-OFF INCH EQUIVALENTS FOR
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 31. 20-Lead Plastic Leaded Chip Carrier [PLCC] (P-20) Dimensions shown in inches and (millimeters)

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option
ADG211AKN	−40°C to +85°C	16-Lead PDIP	N-16
ADG211AKNZ	-40°C to +85°C	16-Lead PDIP	N-16
ADG211AKPZ	-40°C to +85°C	20-Lead PLCC	P-20
ADG211AKR	-40°C to +85°C	16-Lead SOIC_N	R-16
ADG211AKRZ	-40°C to +85°C	16-Lead SOIC_N	R-16
ADG211AKRZ-REEL	-40°C to +85°C	16-Lead SOIC_N	R-16
ADG211AKRZ-REEL7	-40°C to +85°C	16-Lead SOIC_N	R-16
ADG212AKNZ	-40°C to +85°C	16-Lead PDIP	N-16
ADG212AKPZ	-40°C to +85°C	20-Lead PLCC	P-20
ADG212AKPZ-REEL	-40°C to +85°C	20-Lead PLCC	P-20
ADG212AKR	-40°C to +85°C	16-Lead SOIC_N	R-16
ADG212AKRZ	-40°C to +85°C	16-Lead SOIC_N	R-16
ADG212AKRZ-REEL	-40°C to +85°C	16-Lead SOIC_N	R-16

¹ Z = RoHS Compliant Part.

NOTES

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